

FORM PTO-1449 (SUBSTITUTE)  U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))				Attorney Docket No.:      Appl. No. GR 98 P 2499  Applicant THOMAS HANEDER ET AL.  Filing Date                      Group Art Unit MARCH 7, 2001			
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EXAMINER INITIALS	A	PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
	A						
	B						
	C						
	D						
	E						
	F						
	G						
	H						
	I						

  

FOREIGN PATENT DOCUMENT							
		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES   NO
FL	J	0459773A2	12/91	Europe	/	/	X
FL	K	0716455A2	06/96	Europe			X
FL	L	0716455A3	06/96	Europe			X
	M						
	N						

  

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)		
FL.		"A Single-Transistor Ferroelectric Memory Cell", Takahashi Nakamura et al., XP 000557557, IEEE, ISSCC, 1995, Technology Directions, Display, Photonics and Ferroelectric Memo, pp. 68-69 and 340

  

EXAMINER	DATE CONSIDERED <span style="font-family: cursive; font-size: 1.2em;">9/9/02</span>
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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